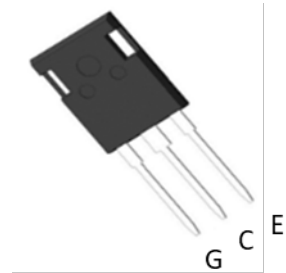


### 650V 40A CoolFAST™ 7 Technology IGBT

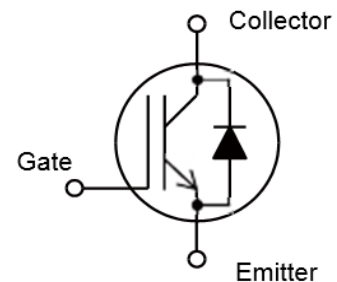
#### Features:

- Low switching power loss
- Low switching surge and noise
- Advanced Fieldstop technology
- Low EMI
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating, halogen-free mold compound, RoHS compliant



#### Applications:

- Industrial UPS
- Welding machine
- Solar converters
- Energy Storage
- Mid to high range switching frequency converters



#### Key Performance and Package Parameters

Type	V <sub>CE</sub>	I <sub>C</sub>	V <sub>CEsat</sub> , T <sub>vj</sub> =25°C	T <sub>vjmax</sub>	Marking	Package
EX40N65HXF	650V	40A	1.6V	175°C	40N65HXF	TO247

#### Maximum Ratings and Characteristics

##### Absolute Maximum Ratings at T<sub>vj</sub>= 25°C (unless otherwise specified)

Items	Symbols	Value	Units
Collector-Emitter voltage	V <sub>CEs</sub>	650	V
Gate-Emitter voltage	V <sub>GES</sub>	±20	V
DC Collector Current, limited by T <sub>vjmax</sub> T <sub>c</sub> = 25°C T <sub>c</sub> = 100°C	I <sub>C</sub>	68 40	A
Pulsed Collector Current, tp limited by T <sub>vjmax</sub>	I <sub>CP</sub>	160	A
Turn-Off Safe Operating Area V <sub>ce</sub> ≤ 1200V, T <sub>j</sub> ≤ 175°C, tp=1μs	-		A
Diode Forward Current, limited by T <sub>vjmax</sub> T <sub>c</sub> = 25°C T <sub>c</sub> = 100°C	I <sub>F</sub>	68 40	A
Turn-Off Safe Operating Area V <sub>ce</sub> ≤ 1200V, T <sub>j</sub> ≤ 175°C, tp=1μs	-		A
Power Dissipation	P <sub>D</sub> 25°C	250	W
Power Dissipation	P <sub>D</sub> 100°C	125	W
Operating Junction Temperature	T <sub>vj</sub>	-55 ~ +175	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +175	°C

### Electrical characteristics at $T_{vj}= 25^{\circ}\text{C}$ (unless otherwise specified)

Description	Symbols	Conditions	Characteristics			Unit
			Min	Typ	Max	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}= 0\text{V}$ , $I_C= 0.50\text{mA}$	650	-	-	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE}= 650\text{V}$ , $V_{GE}= 0\text{V}$	-	-	10	$\mu\text{A}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE}= 0\text{V}$ , $V_{GE}= 20\text{V}$	-	-	100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}= V_{GE}$ , $I_C= 0.5\text{mA}$	4.0	5.0	6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}= 15\text{V}$ , $I_C= 40\text{A}$ , $T_{vj}= 25^{\circ}\text{C}$	-	1.6	2.0	V
		$V_{GE}= 15\text{V}$ , $I_C= 40\text{A}$ , $T_{vj}= 125^{\circ}\text{C}$	-	1.9	-	
		$V_{GE}= 15\text{V}$ , $I_C= 40\text{A}$ , $T_{vj}= 175^{\circ}\text{C}$	-	2.0	-	
Input Capacitance	$C_{ies}$	$V_{CE}= 25\text{V}$ , $V_{GE}= 0\text{V}$ $f= 100\text{kHz}$	-	4192	-	pF
Output Capacitance	$C_{oes}$		-	90	-	pF
Reverse Transfer Capacitance	$C_{res}$		-	4.3	-	pF
Gate Charge	$Q_G$	$V_{CC}= 520\text{V}$ , $I_C= 40\text{A}$ , $V_{GE}= 15\text{V}$	-	76	-	nC
Forward Voltage Drop	$V_F$	$V_{GE}=0\text{ V}$ , $I_F=40\text{ A}$ , $T_{vj}= 25^{\circ}\text{C}$	-	1.85	2.2	V
		$V_{GE}=0\text{ V}$ , $I_F=40\text{ A}$ , $T_{vj}= 125^{\circ}\text{C}$	-	1.7	-	
		$V_{GE}=0\text{ V}$ , $I_F=40\text{ A}$ , $T_{vj}= 175^{\circ}\text{C}$	-	1.65	-	

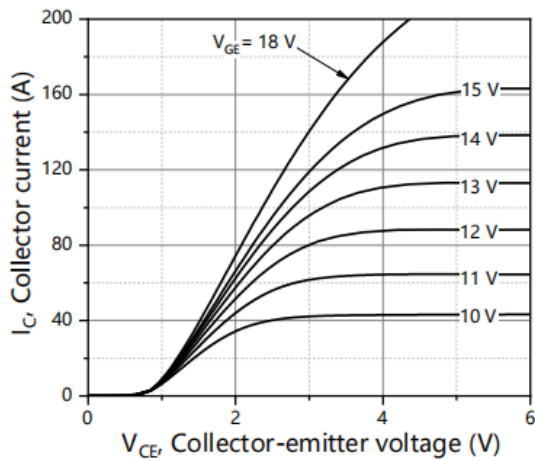
### Switching Characteristics at $T_{vj}=25^{\circ}\text{C}$

Description	Symbols	Conditions	Characteristics			Unit
			Min	Typ	Max	
IGBT Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}= 400V$ $I_C= 40A$ $V_{GE}= 15V$ $R_G= 10\Omega$	-	48	-	ns
Rise Time	$t_r$		-	78	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	152	-	ns
Fall Time	$t_f$		-	46	-	ns
Turn-On Energy	$E_{on}$		-	1.36	-	mJ
Turn-Off Energy	$E_{off}$		-	0.42	-	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}= 400V$ $I_C= 20A$ $V_{GE}= 15V$ $R_G= 10\Omega$	-	45	-	ns
Rise Time	$t_r$		-	29	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	141	-	ns
Fall Time	$t_f$		-	27	-	ns
Turn-On Energy	$E_{on}$		-	0.45	-	mJ
Turn-Off Energy	$E_{off}$		-	0.23	-	mJ
Diode Characteristics						
Diode Reverse Recovery Time	$t_{rr}$	$V_R= 400V$	-	131	-	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_F= 40A$	-	1.0	-	$\mu C$
Diode peak reverse recovery current	$I_{rrm}$	$di_F/dt= 500A/\mu s$	-	16.5	-	A

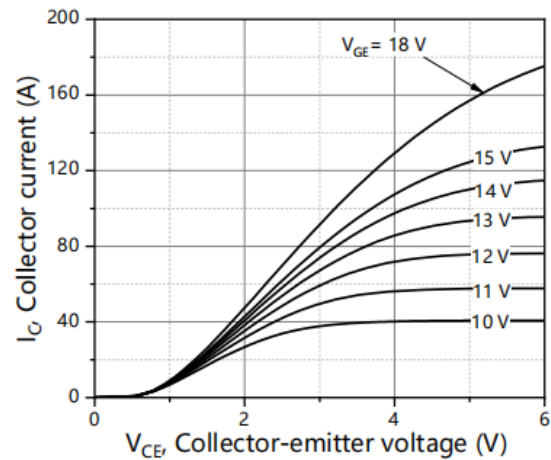
### Thermal resistance

Items	Symbols	Characteristics			Unit
		Min	Typ	Max	
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	40	$^{\circ}\text{C} / \text{W}$
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}$	-	-	0.6	
Thermal Resistance, Diodes Junction to Case	$R_{th(j-c)}$	-	-	1.8	

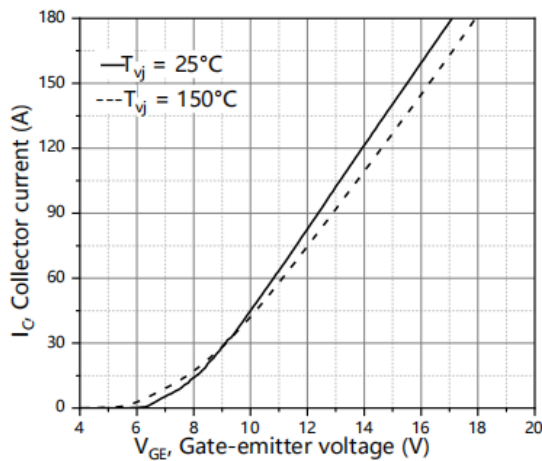
### Electrical Characteristics Diagrams



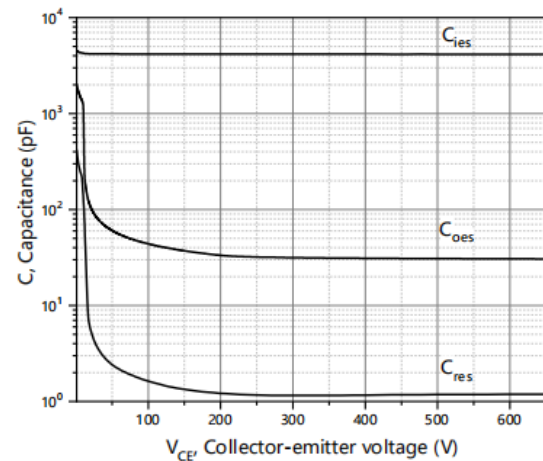
**Figure 1. Typical output characteristics**  
( $T_{vj}=25^{\circ}\text{C}$ )



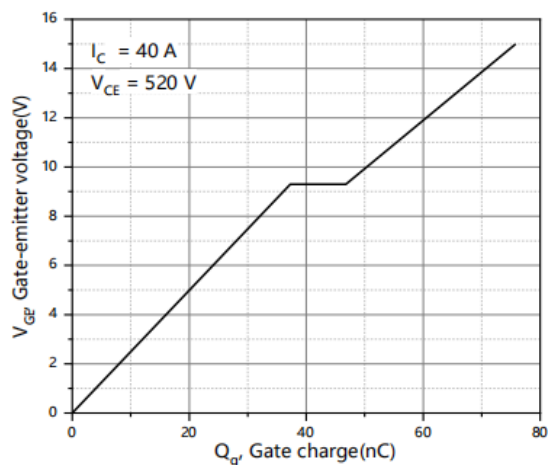
**Figure 2. Typical output characteristics**  
( $T_{vj}=150^{\circ}\text{C}$ )



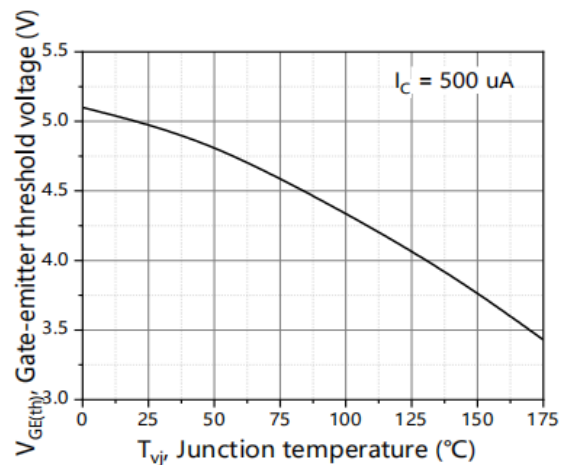
**Figure 3. Typical transfer characteristics**  
( $V_{ce}=20\text{V}$ )



**Figure 4. Typical capacitance**  
( $V_{ge}=0\text{V}$ ,  $f=100\text{ kHz}$ )



**Figure 5. Typical gate charge**



**Figure 6. Gate-emitter threshold voltage**

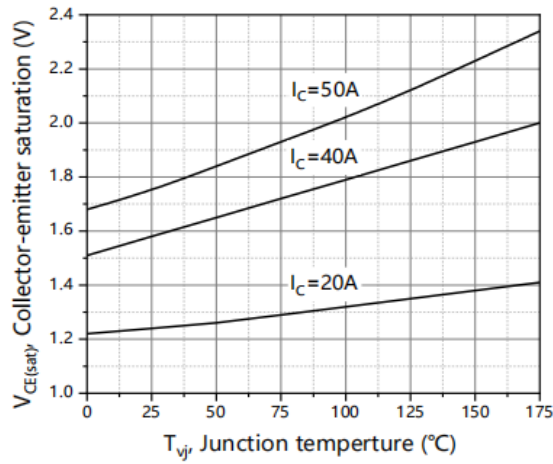


Figure 7. Typical collector-emitter voltage

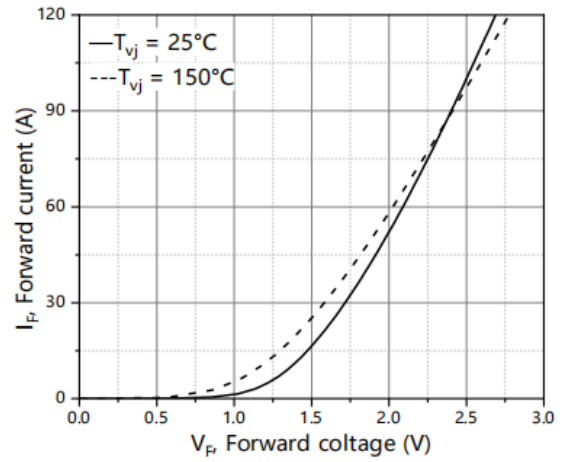


Figure 8. Forward characteristic of diode

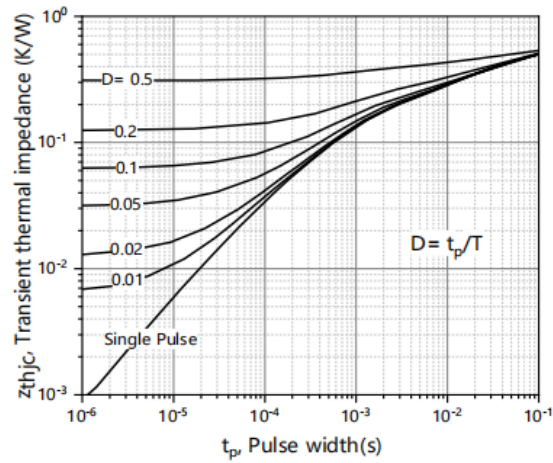


Figure 9. IGBT transient thermal impedance

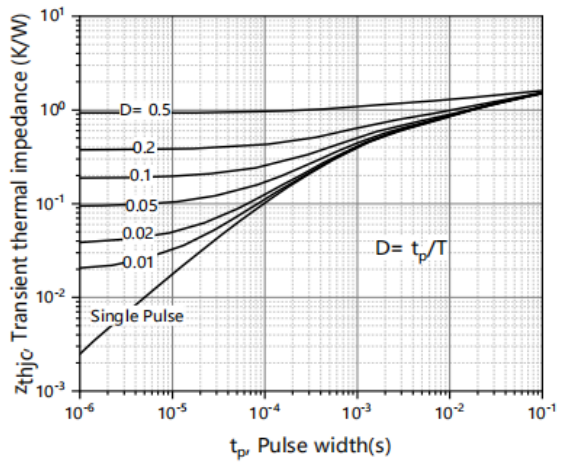
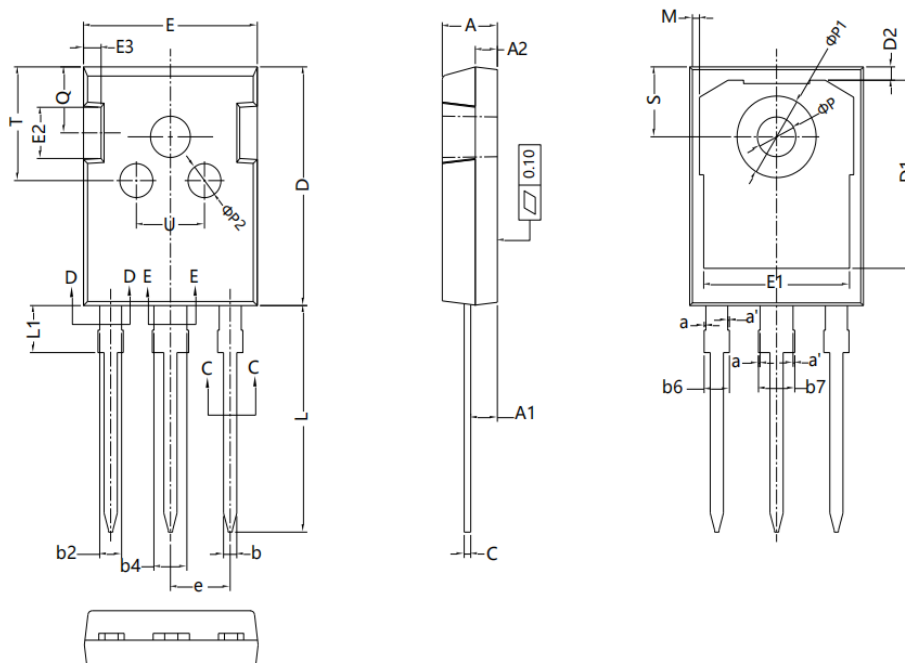


Figure 10. Diode transient thermal impedance

### TO247 Package Outline



Symbol	mm		
	Min	Nom	Max
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0.00	-	0.15
a'	0.00	-	0.15
b	1.16	-	1.26
b2	1.96	-	2.06
b4	2.96	-	3.06
b6	-	-	2.25
b7	-	-	3.25
c	0.59	-	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.40	4.50	4.60
E3	1.50	1.60	1.70
e	5.436 BSC		
L	19.80	19.92	20.10
L1	-	-	4.30
M	0.35	-	0.95
P	3.40	3.50	3.60
P1	7.00	-	7.40
P2	2.40	2.5	2.6
Q	5.60	-	6.0
S	6.05	6.15	6.25
T	9.8	-	10.20
U	6.00	-	6.40

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